Specifcation of products

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

SYMBOL	CHARACTERISTIC	TEST CONDI TIONS	T_j (℃)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean for ward current	180° half sine wave 50Hz Single side cooled, T_C =100°C	150			300	A
$I_{F(RMS)}$	RMS for ward current	Single side cooled, T_C =100°C	150			471	A
V_{RRM}	Repetitive peak reverse voltage	V_{RRM} tp=10ms V_{RsM}= V_{DRM}&V_{RRM}+200V	150	600		1800	V
I_{RRM}	Repetitive peak current	at V_{RRM}	150			20	mA
I_{FSM}	Surge for ward current	10ms half sine wave	150			12.5	KA
I^2t	I^2T for fusing coordination	V_R=0.6V_{RRM}				797	A^2s*10^3
V_{FS}	Threshold voltage					0.75	

OUTLINE DR AWING & CIRCUIT DIAGRAM

Rating and Characteristic

Fi

Outside Dimension



